

SENSITIVE GATE TRIACS

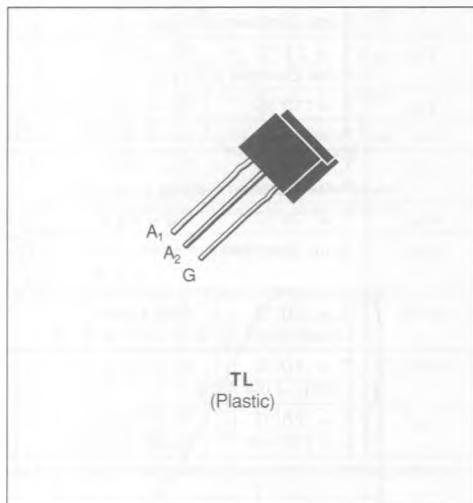
- GLASS PASSIVATED CHIP
- HIGH SURGE CURRENT

DESCRIPTION

Low power triacs suited for 50 and 60 Hz up to 380 V _{RMS}.

APPLICATIONS

- CONTROL SPEED FOR LITTLE MOTORS ; ELECTRIC PUMP OR VENTILATOR, SEWING MACHINE
- RELAY, DETECTOR, ALARM SYSTEM
- ELECTRONIC STARTER FOR LAMP
- HIGH POWER TRIAC DRIVER



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
I _{T(RMS)}	RMS on-state Current (360° conduction angle)	1	A
I _{T(RMS)}	RMS on-state Current on Printed Circuit (360° conduction angle)	0.77	A
I _{TSM}	Non Repetitive Surge Peak on-state Current (T _j initial = 25 °C - Half sine wave)	16	A
		15	
I ² t	I ² t Value for Fusing	1.125	A ² s
di/dt	Critical Rate of Rise of on-state Current (1)	10	A/μs
T _{stg} T _j	Storage and Operating Junction Temperature Range	- 40 to 150	°C
		- 40 to 110	°C

Symbol	Parameter	TLC111S	TLC221S	TLC331S	TLC381S	Unit
V _{DRM}	Repetitive Peak off-state Voltage (2)	200	400	600	700	V

(1) I_G = 100 mA di/dt = 1 A/μs

(2) T_j = 110 °C.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th (P-A)}	Junction to Ambient on Printed Circuit	75	°C/W
R _{th (J-L)}	Junction-leads for 360° Conduction Angle (F = 50 Hz)	45	°C/W

GATE CHARACTERISTICS (maximum values)

$P_{GM} = 2 \text{ W}$ ($t_p = 10 \mu\text{s}$) $I_{GM} = 1 \text{ A}$ ($t_p = 10 \mu\text{s}$)
 $P_G(\text{AV}) = 0.1 \text{ W}$ $V_{GM} = 16 \text{ V}$ ($t_p = 10 \mu\text{s}$)

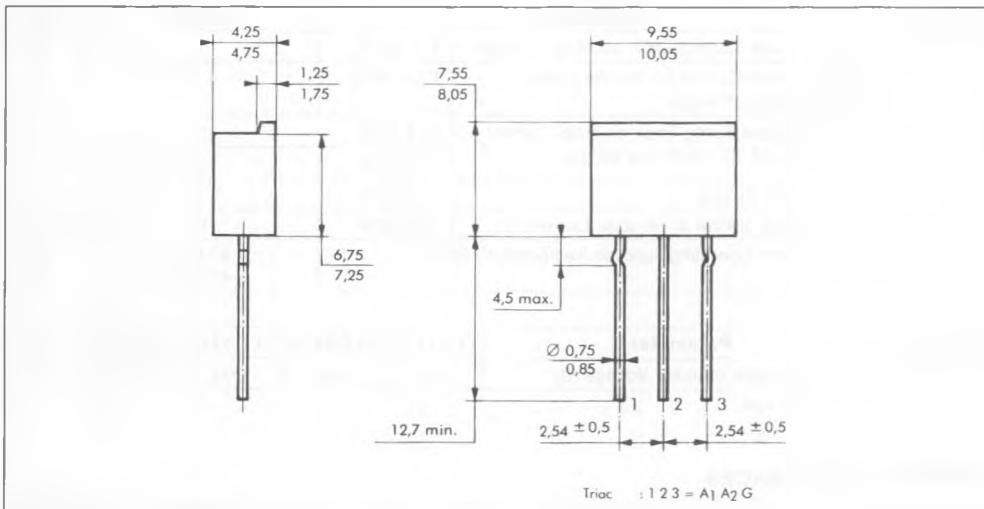
ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Quadrants	Min.	Typ.	Max.	Unit
I_{GT}	$T_j = 25^\circ\text{C}$	$V_D = 12 \text{ V}$	$R_L = 33 \Omega$	I-II-III-IV			10	mA
	Pulse Duration > 20 μs							
V_{GT}	$T_j = 25^\circ\text{C}$	$V_D = 12 \text{ V}$	$R_L = 33 \Omega$	I-II-III-IV			1.5	V
	Pulse Duration > 20 μs							
V_{GD}	$T_j = 110^\circ\text{C}$	$V_D = V_{DRM}$	$R_L = 3.3 \text{ k}\Omega$	I-II-III-IV	0.2			V
I_H^*	$T_j = 25^\circ\text{C}$	$I_T = 100 \text{ mA}$	Gate Open				25	mA
I_L	$T_j = 25^\circ\text{C}$	$V_D = 12 \text{ V}$	$I_G = 20 \text{ mA}$	I-II-III-IV			25	mA
	Pulse Duration > 20 μs							
V_{TM}^*	$T_j = 25^\circ\text{C}$	$I_{TM} = 1.4 \text{ A}$	$t_p = 10 \text{ ms}$				1.8	V
I_{DRM}^*	V_{DRM} Specified		$T_j = 25^\circ\text{C}$				0.01	mA
			$T_j = 110^\circ\text{C}$				0.75	
dv/dt^*	$T_j = 110^\circ\text{C}$	Gate Open Linear Slope up to $V_D = 67\% V_{DRM}$				20		V/ μs
$(dv/dt)_c^*$	$T_j = 40^\circ\text{C}$	$V_D = V_{DRM}$	$I_T = 1.4 \text{ A}$			5		V/ μs
t_{gt}	$T_j = 25^\circ\text{C}$	$V_D = V_{DRM}$	$I_T = 1.4 \text{ A}$	I-II-III-IV		3		μs
	$I_G = 100 \text{ mA}$	$dv/dt = 1 \text{ A}/\mu\text{s}$						

* For either polarity of electrode A₂ voltage with reference to electrode A₁.

PACKAGE MECHANICAL DATA

TL Plastic



Cooling method : by convection (method A)

Marking : type number

Weight : 0.8 g.

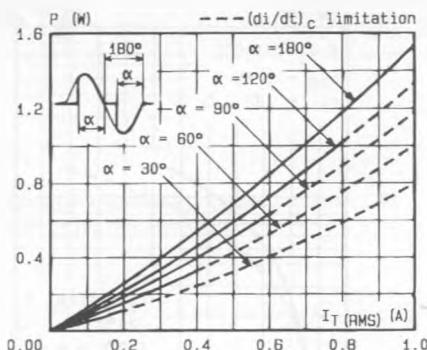


Fig.1 - Maximum mean power dissipation versus RMS on-state current ($F = 60$ Hz).

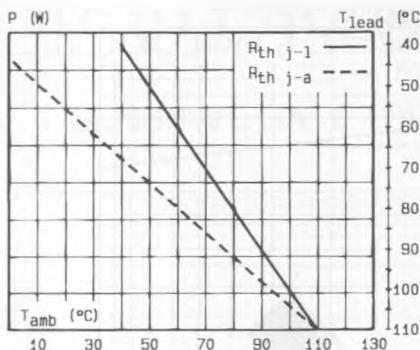


Fig.2 - Correlation between maximum mean power dissipation and maximum allowable temperatures (T_{amb} and T_{lead}) resistances heatsink + contact.

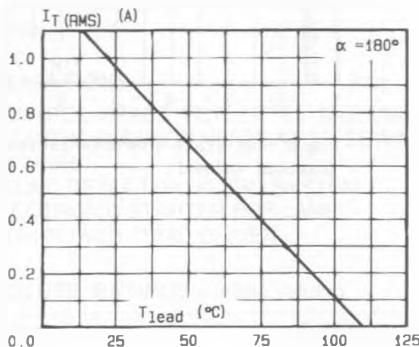


Fig.3 - RMS on-state current versus lead temperature.

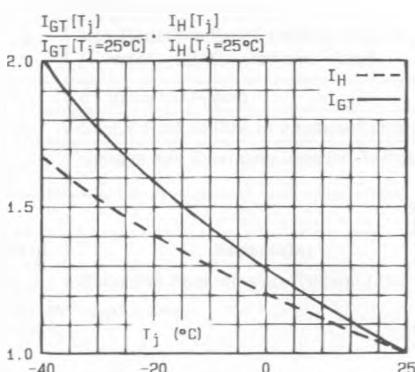


Fig.5 - Relative variation of gate trigger current and holding current versus junction temperature.

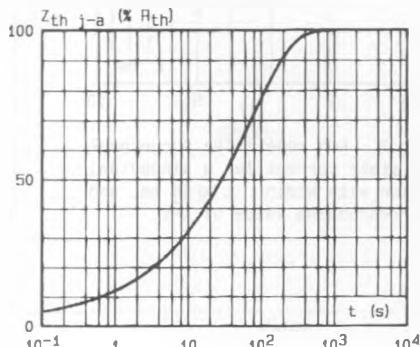


Fig.4 - Thermal transient impedance junction to ambient versus pulse duration.

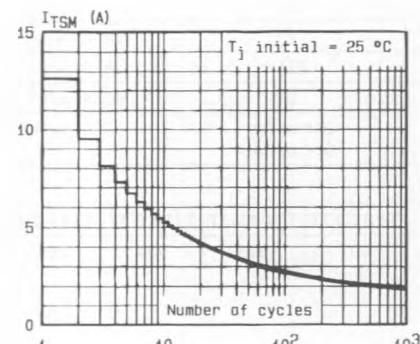


Fig.6 - Non repetitive surge peak on state current versus number of cycles.

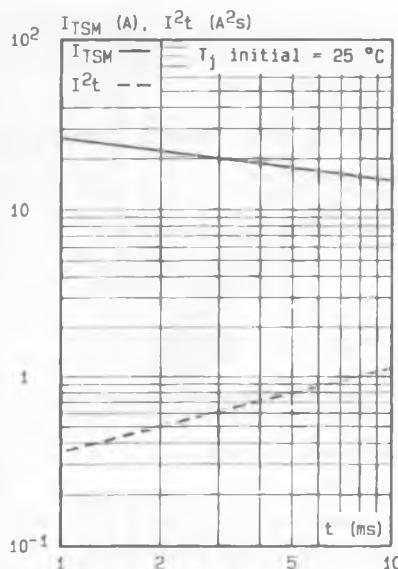


Fig.7 - Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10$ ms, and corresponding value of I^2t .

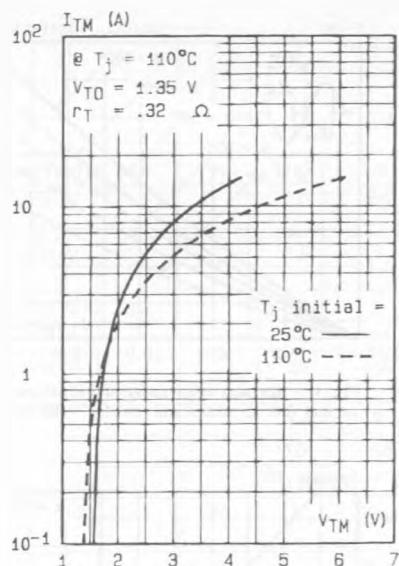


Fig.8 - On-state characteristics (maximum values).